

Corrigendum

Plasticity-induced oxidation reactivity on Ni(100) studied by scanning tunneling spectroscopy – CORRIGENDUM

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Figure 2 as published is missing an axis label.

The corrected Figure 2 appears below.

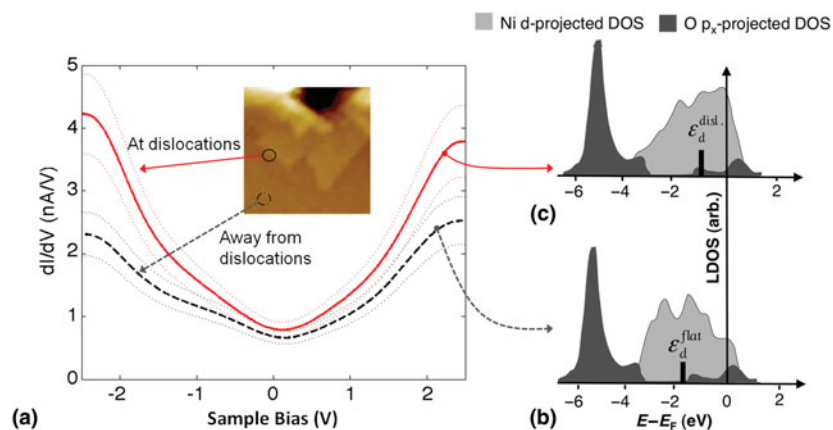


Figure 2. (a) In situ electronic structure characterization of the Ni(100) surface upon STM tip-induced plasticity. Differential tunneling conductance measurements, dI/dV , obtained both at dislocation steps (solid curve) and away from dislocations (dashed curve). Each curve is the average of over 100 point spectra from three different indentations. The error in dI/dV measured by standard deviation is $\pm 18\%$, represented by dashed enveloping curves. Schematic density of state diagrams illustrate how an increase in DOS around E_F can be interpreted as an up-shift in the Ni d-band center from (b) ϵ_d^{flat} at the undamaged surface to (c) ϵ_d^{disl} at dislocations (after [14]).

Reference

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